

HPSI Silicon Carbide & GaN Epitaxy

PROVEN EXPERTISE IN SILICON & GaN MATERIALS FOR RF APPLICATIONS

FULLY INTEGRATED SUBSTRATE AND EPITAXY SUPPLIER

Wolfspeed offers the industry's broadest range of Silicon Carbide and GaN on Silicon Carbide materials, including semi-insulating substrates and nitride epitaxy options up to the newly available diameter of 150mm. Backed by more than 30 years of Silicon Carbide development and manufacturing experience, Wolfspeed materials deliver world-leading bandwidth, efficiency and frequency of operation for telecom, aerospace and defense applications.

When you partner with Wolfspeed, you get the best and most innovative materials.

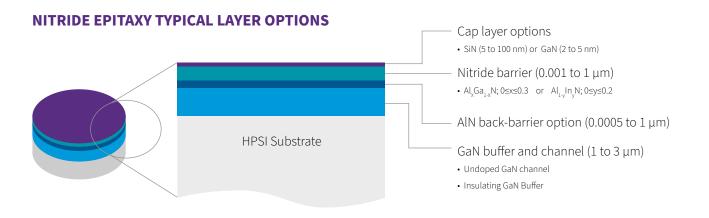
HIGH PURITY SEMI-INSULATING PORTFOLIO

Polytype	Supported Diameters	Nitride Epitaxy	
4H	100 mm	GaN, AlN	SiN
	150 mm	AlGaN, AlInN	HEMT structures



HIGH PURITY SEMI-INSULATING SILICON CARBIDE SUBSTRATE PRODUCT DESCRIPTIONS

Part Number	Description	
W4TRF0R-0200	4H-SiC, HPSI, Research Grade, 100mm, On-Axis, ≥1E6 Ω-cm, Standard MPD, 500um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate	
W4TPF0R-0200	4H-SiC, HPSI, Production Grade, 100mm, On-Axis, ≥1E6 Ω-cm, Standard MPD, 500um Thick w/ 32.5mm Flat, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate	
W4TRG0R-N-0200	4H-SiC, HPSI, Research Grade, 150mm, On-Axis, ≥1E6 Ω-cm, Standard MPD, 500um Thick w/ Notch, Double-Sided Polish Si Face CMP Epi Ready, Bare Substrate	
W4TPG0R-N-0200	4H-SiC, HPSI, Production Grade, 150mm, On-Axis, ≥1E6Ω-cm, Standard MPD, 500um Thick w/ Notch, Double- Sided Polish Si Face CMP Epi Ready, Bare Substrate	



Each structure is built to customer provided specifications.

Custom structures ouside of typical layer options and quaternary compositions available upon special request.

